

SHARP

TO: \_\_\_\_\_

REFERENCE

DEVICE SPECIFICATION FOR

64K bit STATIC RAM (8,192 X 8bit)  
 MODEL NO.  
**L H 5 1 6 0 H N - 1 0 L**  
 ( LH5160N8 )

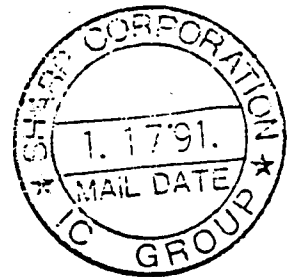
SPEC NO.: EL02Y011

ISSUE: Dec. 13. 1990

CUSTOMERS APPROVAL

DATE: \_\_\_\_\_

BY: \_\_\_\_\_



PRESENTED

BY: \_\_\_\_\_

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Integrated Circuit Group

SHARP CORPORATION

EL-02-2966

## 1. General Description

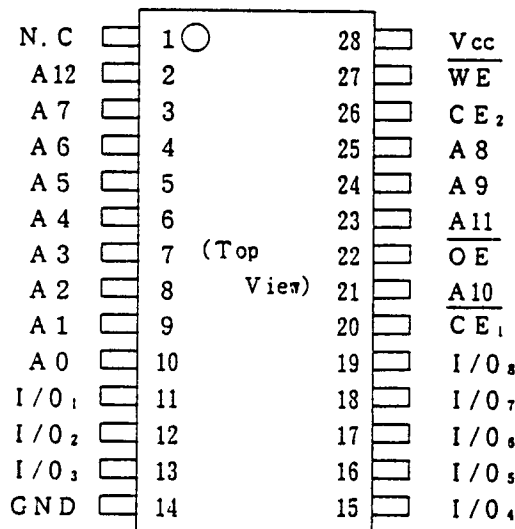
LH5160HN 10L is a static RAM organized as 8.192 word × 8 bit fabricated with a CMOS silicon gate process.

It's main features include:

### Features

- High speed Access time . . . . 100 ns (MAX.)
- Current consumption
  - Operating . . . . 40 mA (MAX.)
  - Standby ~70°C . . . . 1.0 μA (MAX.)
  - ~85°C . . . . 3.0 μA (MAX.)
  - Data hold . . . . 0.2 μA (Vcc=3V, Ta=25°C)
- Single 5V power supply 5V ± 10%
- Fully static operation
- All input/output TTL compatible
- Three-state output
- Not designed or rated as radiation hardened
- 28 pin SOP plastic package
- P-type bulk silicon
- Operating temperature is -40 ~ 85°C
- Pin configuration is compatible with industry standard 64K EPROM

## 2. Pin Configuration



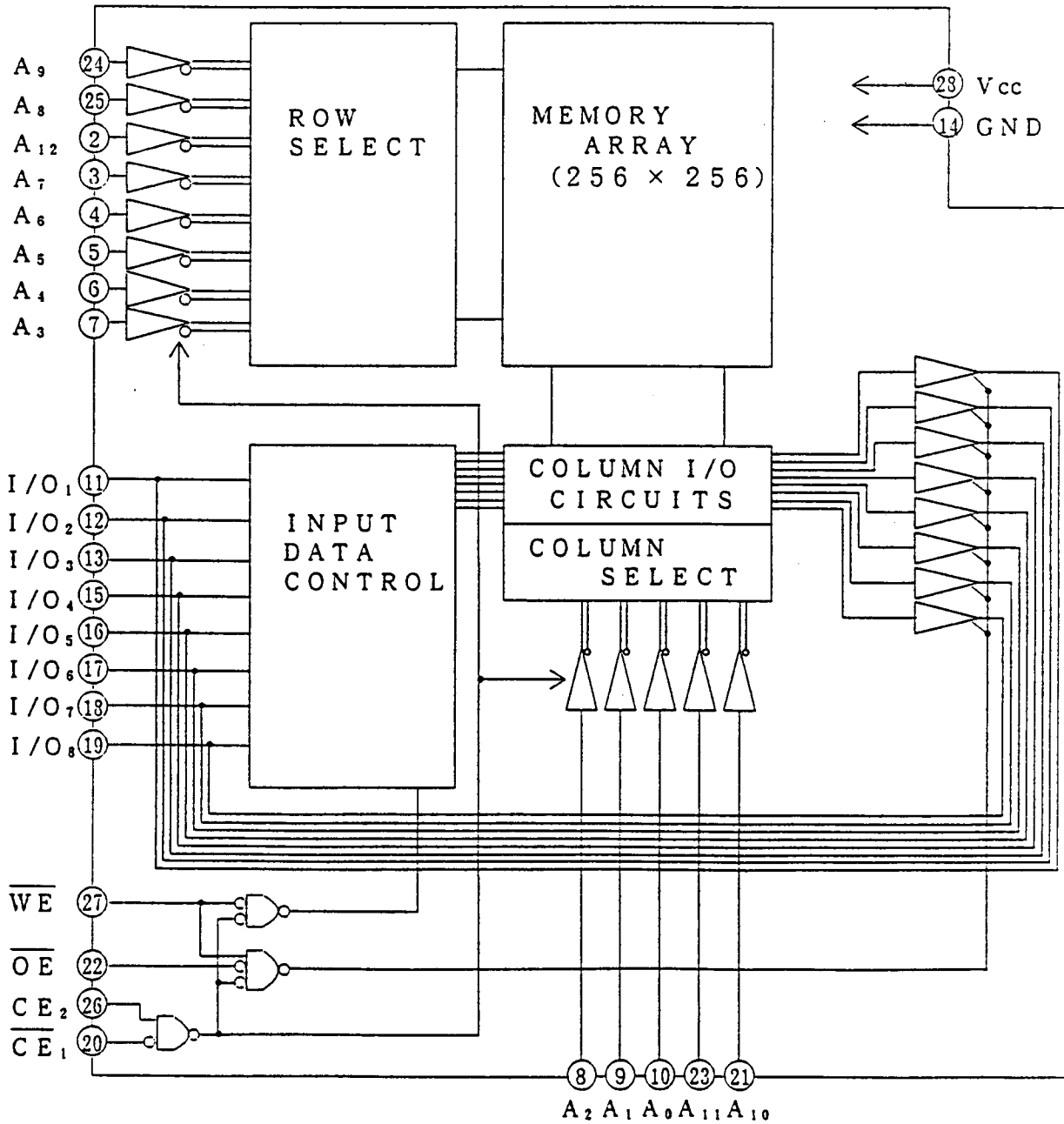
Pin Name	Signal
A <sub>0</sub> ~ A <sub>12</sub>	Address input
$\overline{CE}_1/\overline{CE}_2$	Chip enable
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
I/O <sub>1</sub> ~ I/O <sub>8</sub>	Data input/output
Vcc	Power supply
GND	Ground
N.C.	Non connection

### 3. Operating Mode

$\overline{CE}_1$	$CE_2$	$\overline{WE}$	$\overline{OE}$	Mode	I/O <sub>1</sub> ~I/O <sub>8</sub>	Supply current
H	X	X	X	Deselect	High Z	Standby (I <sub>cc1</sub> )
X	L	X	X			
L	H	L	X	Write	D <sub>IN</sub>	Operating (I <sub>cc</sub> )
L	H	H	L	Read	D <sub>OUT</sub>	Operating (I <sub>cc</sub> )
L	H	H	H	Output disable	High Z	Operating (I <sub>cc</sub> )

X : H or L

### 4. Block Diagram



## 5. Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Supply voltage*	V <sub>CC</sub>	-0.3~+7.0	V
Input voltage *	V <sub>IN</sub>	-0.3~V <sub>CC</sub> +0.3	V
Operating temperature	T <sub>opt</sub>	-40~+85	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

\* Maximum applicable voltage on any pin with respect to GND

## 6. Recommended DC Operating Conditions

(T<sub>a</sub> = -40~+85°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V <sub>CC</sub>	4.5	5.0	5.5	V
Input voltage	V <sub>IH</sub>	2.2		V <sub>CC</sub> +0.3	V
	V <sub>IL</sub>	-0.3		0.8	V

## 7. DC Electrical Characteristics

(T<sub>a</sub> = -40~+85°C, V<sub>CC</sub> = 5 V ± 10%)

Parameter	Symbol	Conditions	Min.	Max.	Unit
Input leakage current	I <sub>LI</sub>	V <sub>IN</sub> = 0 ~ V <sub>CC</sub>		1.0	μA
Output leakage current	I <sub>LO</sub>	$\overline{CE}_1 = V_{IH}$ or $CE_2 = V_{IL}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$ V <sub>I/O</sub> = 0 ~ V <sub>CC</sub>		1.0	μA
Operating Supply current	I <sub>CC</sub>	$\overline{CE}_1 = V_{IL}$ , V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> CE <sub>2</sub> = V <sub>IH</sub> , Output open		40	mA
Standby current	I <sub>CC1</sub>	$\overline{CE}_1 = V_{IH}$ or CE <sub>2</sub> = V <sub>IL</sub>		10	mA
		CE <sub>2</sub> ≤ 0.2V or CE <sub>1</sub> ≥ V <sub>CC</sub> - 0.2V *	~+70°C	1.0	μA
	I <sub>CC2</sub>	CE <sub>2</sub> ≤ 0.2V or CE <sub>1</sub> ≥ V <sub>CC</sub> - 0.2V *	~+85°C	3.0	μA
Output voltage	V <sub>OL</sub>	I <sub>OL</sub> = 2.1mA		0.4	V
	V <sub>OH</sub>	I <sub>OH</sub> = -1mA	2.4		V

\* CE<sub>2</sub> ≥ V<sub>CC</sub> - 0.2V or CE<sub>2</sub> ≤ 0.2V

## 8. Test Condition of AC Characteristics

Input pulse level	0.6~2.4 V
Input rise/fall time	10 ns
Input/Output timing level	1.5 V
Output load	1 TTL + C <sub>L</sub> = 100 pF

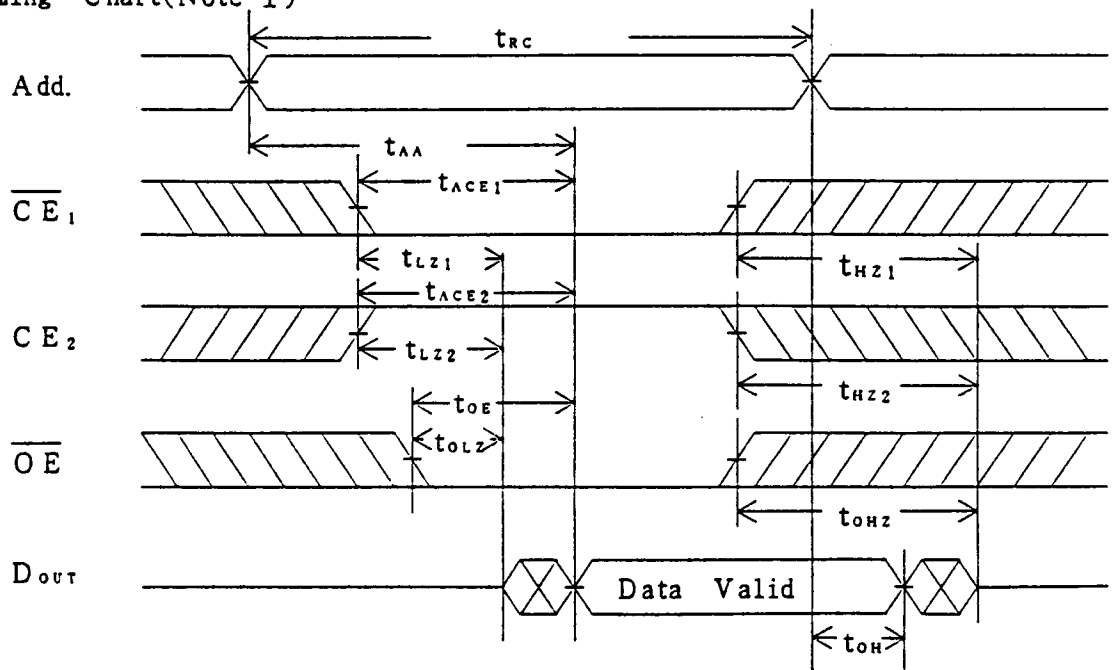
## 9. AC Characteristics

Read cycle

(Ta = -40~85°C, Vcc = 5 V ± 10%)

Parameter	Symbol	Min.	Max.	Unit
Read cycle time	$t_{RC}$	100		ns
Address access time	$t_{AA}$		100	ns
Chip enable access time with respect to $\overline{CE}_1$	$t_{ACE1}$		100	ns
Chip enable access time with respect to $\overline{CE}_2$	$t_{ACE2}$		100	ns
Output enable access time	$t_{OE}$		40	ns
Output hold time	$t_{OH}$	10		ns
Output floating hold time with respect to $\overline{CE}_1$	$t_{LZ1}$	10		ns
Output floating hold time with respect to $\overline{CE}_2$	$t_{LZ2}$	10		ns
Output floating time with respect to $\overline{OE}$	$t_{OLZ}$	5		ns
Output floating time with respect to $\overline{CE}_1$	$t_{HZ1}$	0	30	ns
Output floating time with respect to $\overline{CE}_2$	$t_{HZ2}$	0	30	ns
Output floating time with respect to $\overline{OE}$	$t_{OHZ}$	0	20	ns

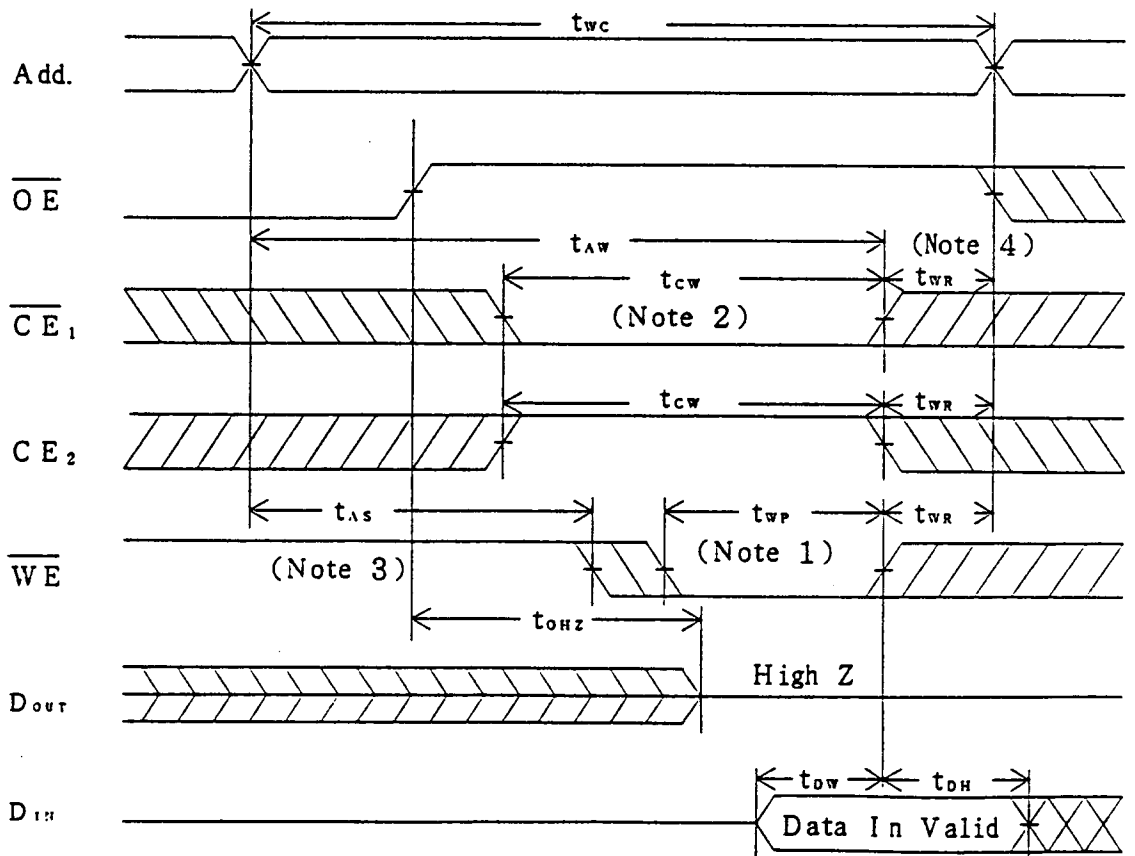
Timing Chart(Note 1)

Note1)  $\overline{WE}$  is "High" level during the read cycle

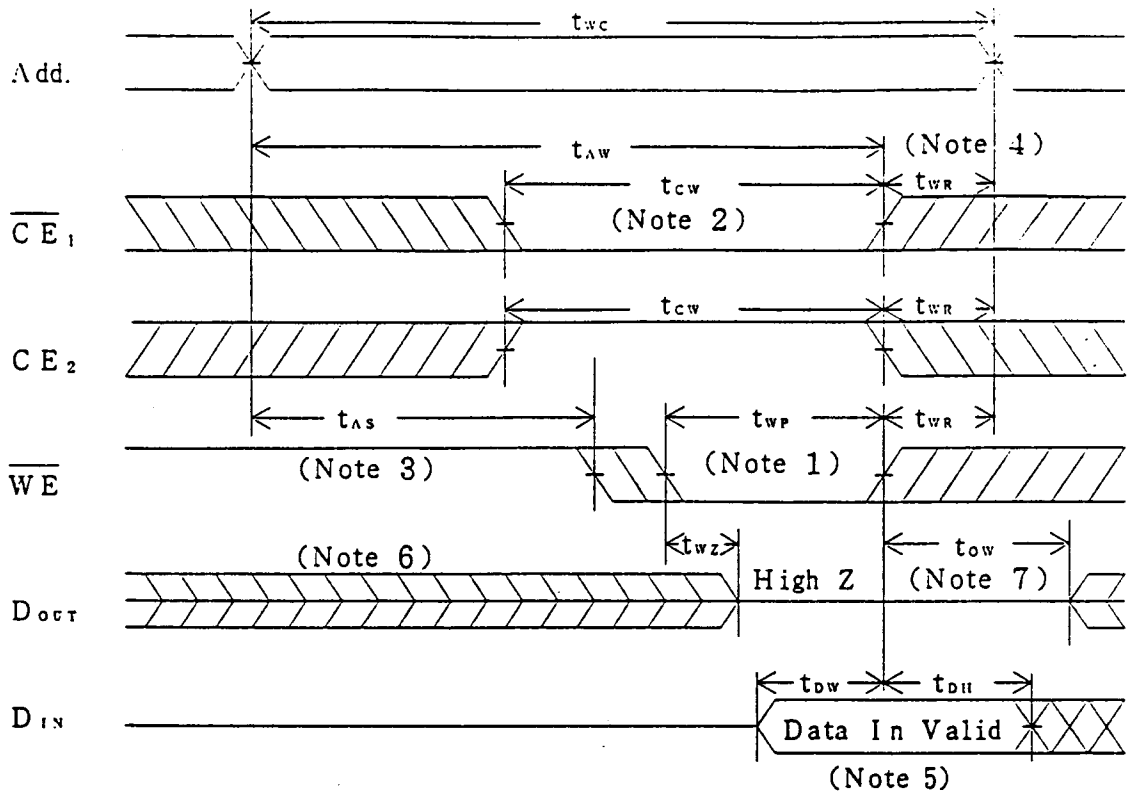
## Write cycle

( $T_a = -40 \sim 85^\circ\text{C}$ ,  $V_{cc} = 5\text{V} \pm 10\%$ )

Parameter	Symbol	Min.	Max.	Unit
Write cycle time	$t_{wc}$	100		ns
Chip enable time to write	$t_{cw}$	90		ns
Address valid time	$t_{AW}$	90		ns
Address setup time	$t_{AS}$	20		ns
Write pulse width	$t_{WP}$	60		ns
Write recovery time	$t_{WR}$	10		ns
Input data set time	$t_{DW}$	50		ns
Input data hold time	$t_{DH}$	0		ns
Output floating hold time with respect to $\overline{WE}$	$t_{OW}$	10		ns
Output floating time with respect to $\overline{WE}$	$t_{WZ}$	0	30	ns
Output floating time with respect to $\overline{OE}$	$t_{OHZ}$	0	20	ns



Timing Chart - ( $\overline{OE}$  Low fixed)



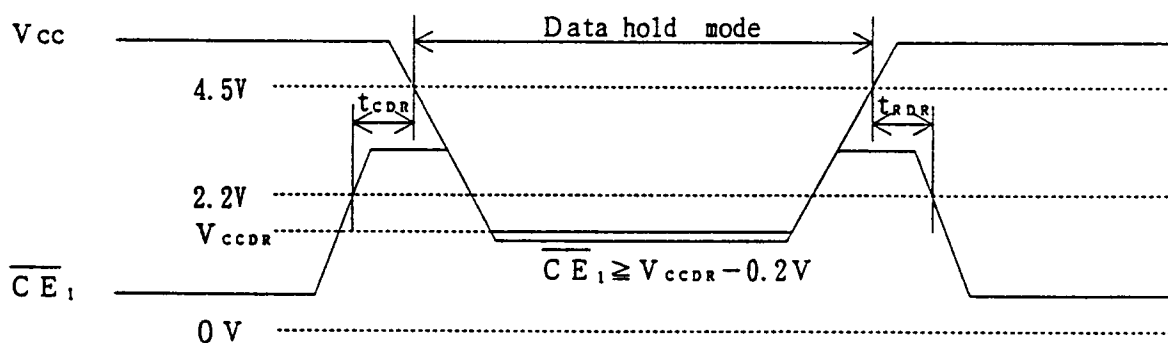
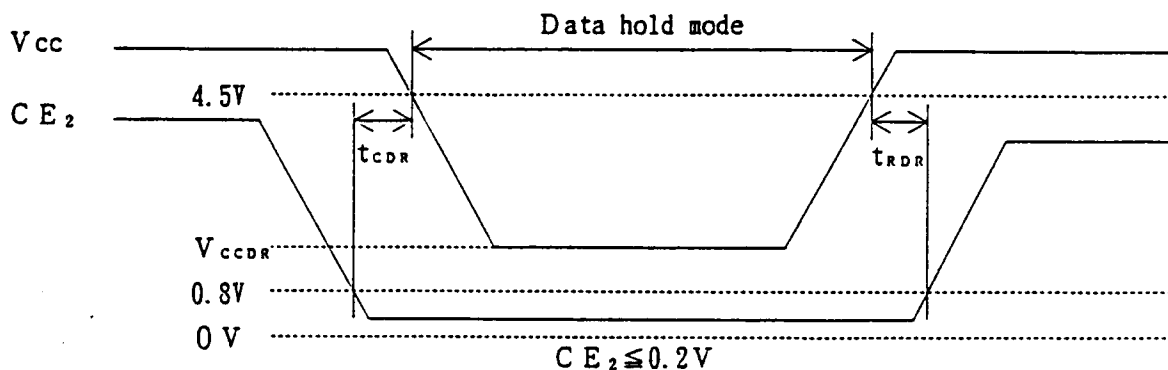
- Note) 1. The writing occurs during a overlapping period of  $\overline{CE}_1 = 'Low'$ ,  $CE_2 = 'High'$  and  $\overline{WE} = 'Low'$  ( $t_{WP}$ ).
2.  $t_{CW}$  is defined as the time from the last occurring transit, either  $\overline{CE}_1$  Low transit or  $CE_2$  High transit, to the time when the writing is finished.
3.  $t_{AS}$  is defined as the time from address change to writing start.
4.  $t_{WR}$  is defined as the time from writing finish to address change.
5. Since during this period, I/O pins assume output state, no input signal  $180^\circ$  out of phase with an output signal admitted.
6. If  $\overline{CE}_1$  Low transit or  $CE_2$  High transit occurs at the same time or after  $\overline{WE}$  Low transit the output will remain High Z.
7. If  $CE_1$  High transit or  $CE_2$  Low transit occurs at the same time or before  $\overline{WE}$  High transit, the output remain High Z.

## 10. Low Voltage Data Hold Characteristics

(Ta = -40 ~ +85°C)

Parameter	Symbol	Condition	Min.	Max.	Unit
Data hold supply voltage	$V_{CCDR}$	$CE_2 \leq 0.2V$ or $\overline{CE}_1 \geq V_{CCDR} - 0.2V$ *	2.0		V
Data hold supply current	$I_{CCDR}$	$V_{CCDR} = 3V$ $CE_2 \leq 0.2V$ or $\overline{CE}_1 \geq V_{CCDR} - 0.2V$ *		0.2 0.4 0.6	$\mu A$
Chip enable setup time	$t_{CDR}$		0		ns
Chip enable hold time	$t_{RDR}$		** $t_{RC}$		ns

 \*  $CE_2 \geq V_{CCDR} - 0.2V$  or  $CE_2 \leq 0.2V$     \*\* Read cycle time

 Timing Chart - ( $\overline{CE}_1$  Control) Note)1

 Timing Chart - ( $CE_2$  Control)


Note)1 To control the data hold mode at  $\overline{CE}_1$ , fix the input level of  $CE_2$  between  $V_{CCDR} \sim V_{CCDR} - 0.2V$  or  $0.0V \sim 0.2V$  during the data hold mode.



## 11. Pin Capacitance

( $T_a = 25^\circ\text{C}$ ,  $f = 1\text{ MHz}$ )

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	$C_{IN}$	$V_{IN} = 0\text{ V}$			7	pF
I/O capacitance	$C_{I/O}$	$V_{I/O} = 0\text{ V}$			10	pF

Note) Parameter is sample value, not all tested.

# SHARP

## PACKAGE AND PACKING SPECIFICATION

### 1. Package Outline Specification

Refer to drawing No. AA 9 3 1

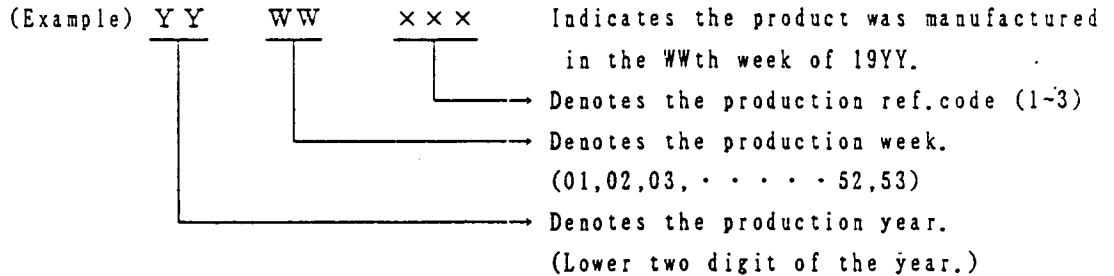
### 2. Markings

#### 2-1. Marking contents

(1) Product name : LH 5 1 6 0 HN - 1 0 L

(2) Company name : SHARP

(3) Date code



(4) The marking of "JAPAN" indicates the country of origin.

#### 2-2. Marking layout

Refer drawing No. AA 9 3 1

(This layout do not define the dimensions of marking character and marking position.)

### 3. Surface Mount Conditions

The conditions below are recommended when mounting ICs not to deteriorate IC quality.

#### 3-1. Soldering conditions

Mounting Method	Temperature and Duration	Measurement Point
Infrared reflow soldering	Peak temperature of 240°C, duration less than 15 seconds above 230°C, temperature increase rate of 1~4°C/second	IC surface
Solder dipping	245°C or less, duration less than 3 seconds/dip, total of 5 seconds	Solder bath
Vapor phase soldering	215°C or less, duration less than 40 seconds above 200°C	Steam
Manual soldering (soldering iron)	260°C or less, duration less than 10 seconds	IC outer lead surface

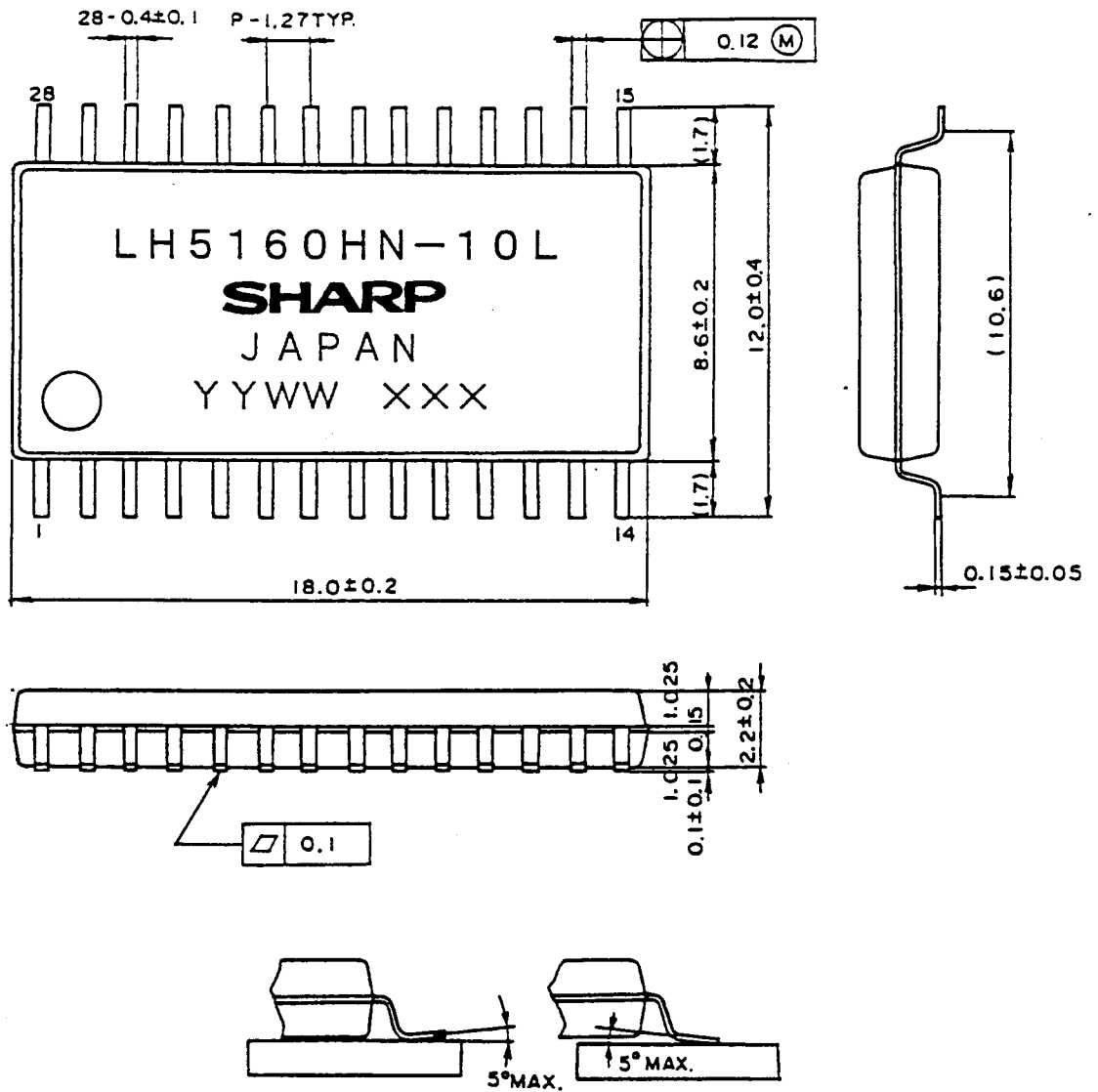
#### 3-2. Conditions for removal of residual flux

(1) Ultrasonic washing power : 25 Watts/liter or less

(2) Washing time : Total 1 minute maximum

(3) Solvent temperature : 15~40°C

ISSUE DATE	'90.12.03	APPROVE	CHECK	DESIGN	DESIGN	(NOTE)
ISSUE NUMBER	H01203-03	<i>T. Tsuda</i>	<i>F. Kurosaki</i>	<i>T. Kimura</i>	<i>T. Awan</i>	
S/C NUMBER	LH5160N8					



名称	リード仕上	TIN-LEAD	単位	備考
NAME SOP28-P-450	LEAD FINISH	PLATING	UNIT mm	プラスチックパッケージ外形寸法は、 バリを含まないものとする。
シャープ株式会社	IC事業本部			NOTE Plastic body dimensions do not include burr of resin.
SHARP CORP.	IC GROUP	DRAWING NO.	AA931	

## 4. Packing Specification (Embossed Carrier Taping Specification)

This standard apply to the embossed carrier taping specification for ICs to be delivered from SHARP CORPORATION. SHARP's embossed carrier taping specification are, in principle, based on those set forth by the EIAJ (Electronic Industries Association of Japan (RC-1009B)) and the EIA (Electronic Industries Association (EIA481A)).

### 4 - 1. Tape Structure

- Embossed carrier tape is made of conductive plastic. The embossed portions of the carrier tape are filled with IC packages and covered with a top covering tape to enclose them.

### 4 - 2. Taping Reel and Embossed Carrier Tape Size

- For the taping reel and embossed carrier tape sizes, refer to the attached drawings (NO. CV524 and CV521)

### 4 - 3. IC Package Enclosure in Embossed Carrier Tape

- The IC package enclosure direction in the embossed portion as it compares to the direction in which the tape is pulled is indicated by an index mark on package (Index mark indicate the NO.1 pin on package) in the attached drawing (NO. CV522).

### 4 - 4. Missing IC Packages inside Embossed Carrier Tape

- The number of missing IC packages inside the embossed carrier tape should not exceed 0.1% of the total enclosed in the tape per reel, or 1, whichever may be larger. There should never be more than two consecutive missing IC package.

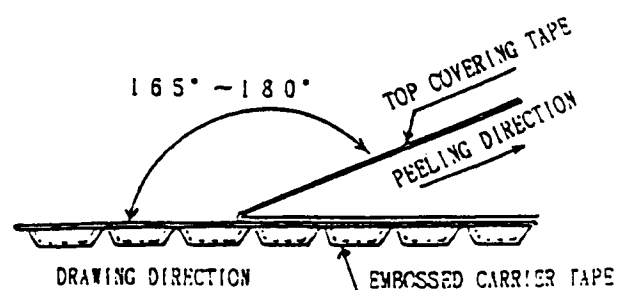
### 4 - 5. Tape Joints

- The embossed carrier tape should not have more than one joint per reel.

### 4 - 6. Peeling Strength of the Top Covering Tape

- Peeling strength must meet the following conditions.

- 1) Peeling angle  
at  $165^{\circ}$  to  $180^{\circ}$
- 2) Peeling speed  
at 300mm/min.
- 3) Peeling strength  
at 0.2 to 0.7N (20 to 70gf)



#### 4 - 7. Packing

- The top covering tape (leader side) at the leading edge of the embossed carrier tape, and the trailing edge of the embossed carrier tape, shall be held in place with paper adhesive tape exceeding 30mm in length.
- The leading and trailing edges of the embossed carrier tape shall be left empty (with embossed portions not filled with IC packages), in the attached drawing (NO. CV522).
- The number of IC packages enclosed in the embossed carrier tape per reel shall, in principle, be as listed below.

Package Type	Number of IC Packages/Reel
SOP14PIN, SOP16PIN	3,000 pcs
SOP24PIN	1,500 pcs
SOP28PIN	1,000 pcs

#### 4 - 8. Indications

- The following shall be indicated on the taping reel and the packing case.
  - 1) Part Number (Product Name)
  - 2) Storage Quantity
  - 3) Production Date
  - 4) Manufacture's Name (SHARP)

Note : The IC taping direction shall be indicated by "E1" or "E2" suffixed to the part number.

E1 : Equivalent to "f" of the EIAJ (RC-1009B) standard.
E2 : Equivalent to "B" of the EIAJ (RC-1009B) standard.

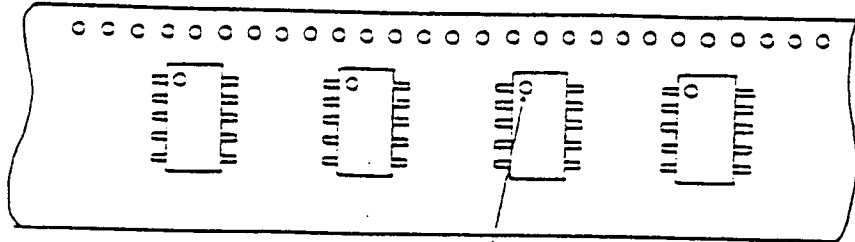
#### 4 - 9. Protection While in Transit

Embossed carrier tape should be free from deformed IC leads and deterioration in electrical characteristics.

EMBOSS TAPING TYPE (E2)

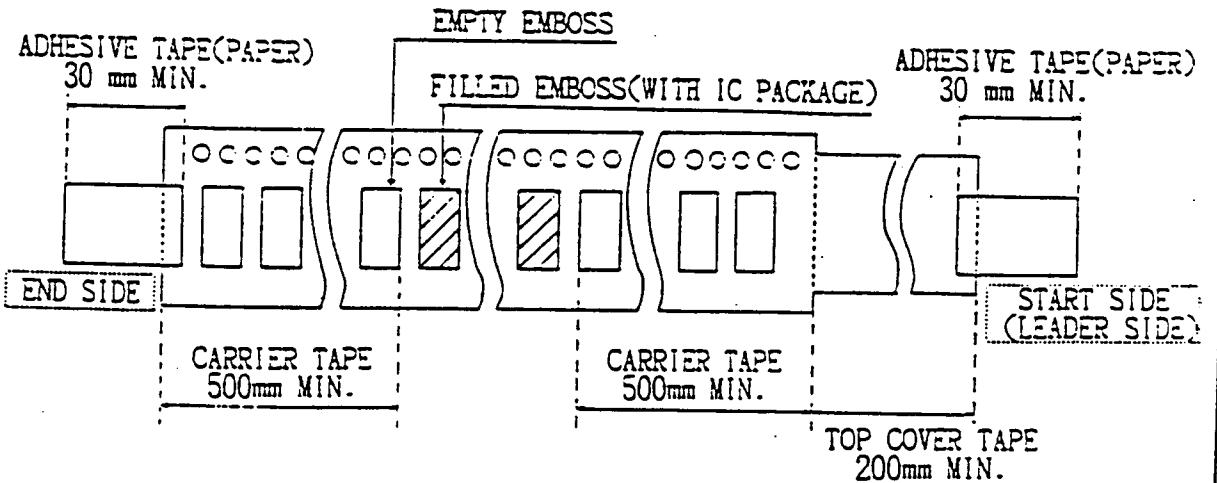
IC TAPING DIRECTION

THE DRAWING DIRECTION OF TAPE

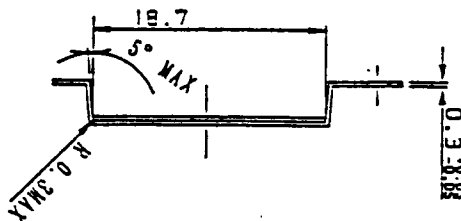
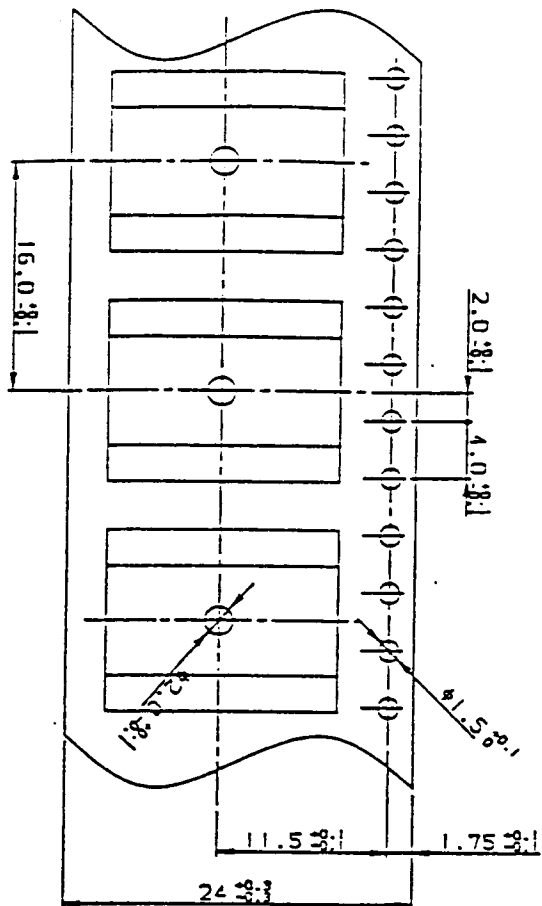
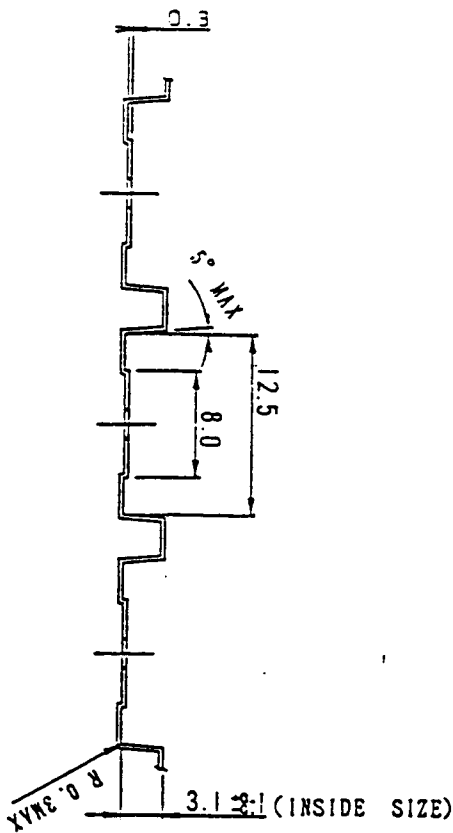


INDEX OF IC PACKAGE  
(Indicate the NO.1 pin of IC package)

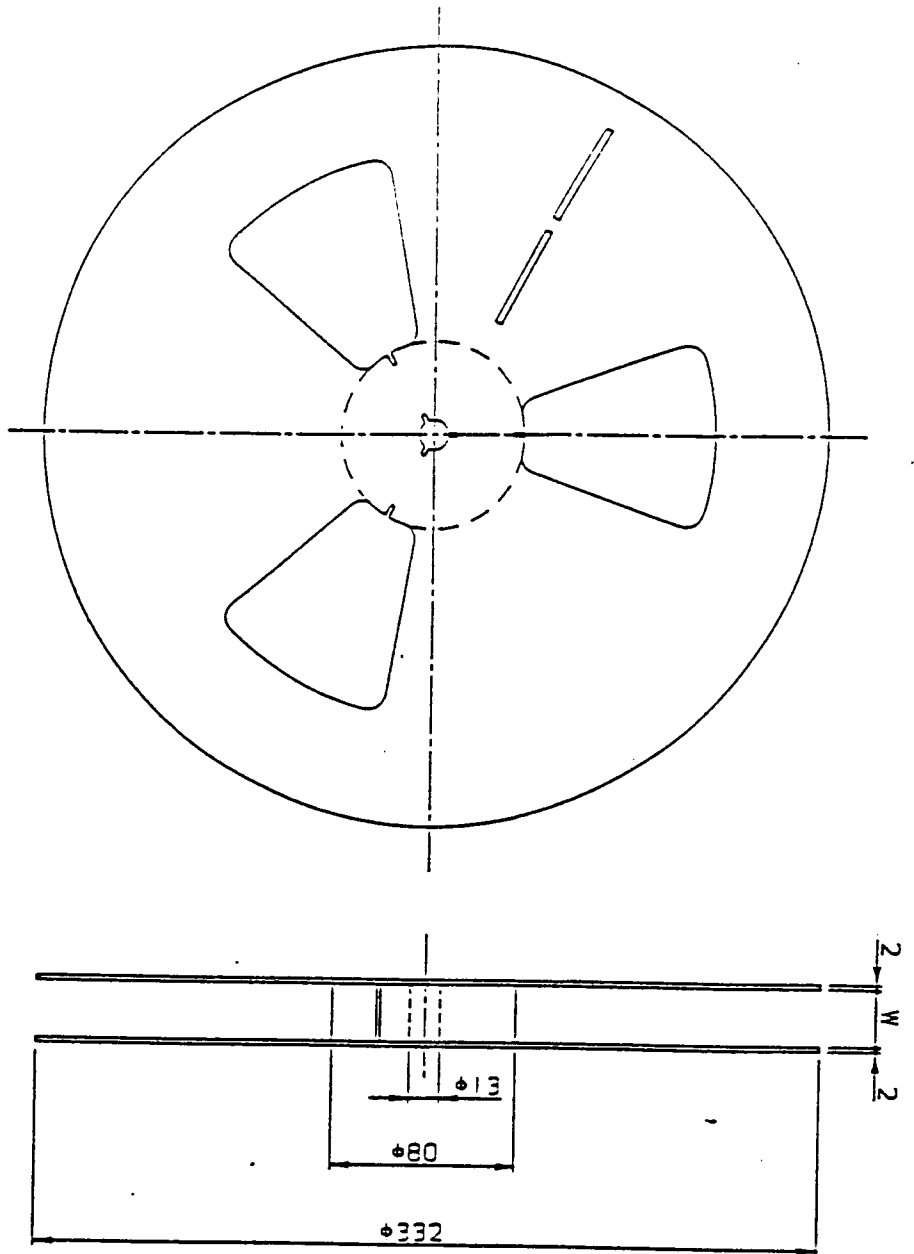
LEADER SIDE AND END SIDE OF TAPE



尺 度 SCALE	单 位 UNIT	△	
/	1 = /	△	
材 質 MATERIAL	仕 上 FINISH	改 訂 日 期 DATE	改 訂 記 事 REVISE
		名 称 NAME	EMBOSS TAPING TYPE (E2)
SHARP CORPORATION		编 号 CODE	
		图 号 DRAWING No	CV 5 2 2



尺度 SCALE	単位 UNIT	△			
1/2	1 = mm/mm	△			
材質 MATERIAL	仕上 FINISH	改訂日 DATE	改訂記事 REVISION	担当者 CHARGE	
CONDUCTIVE PVC					名称 NAME EC28SPS
SHARP CORPORATION		コード CODE			
SHARP CORPORATION		図番 DRAWING No.	CV524		

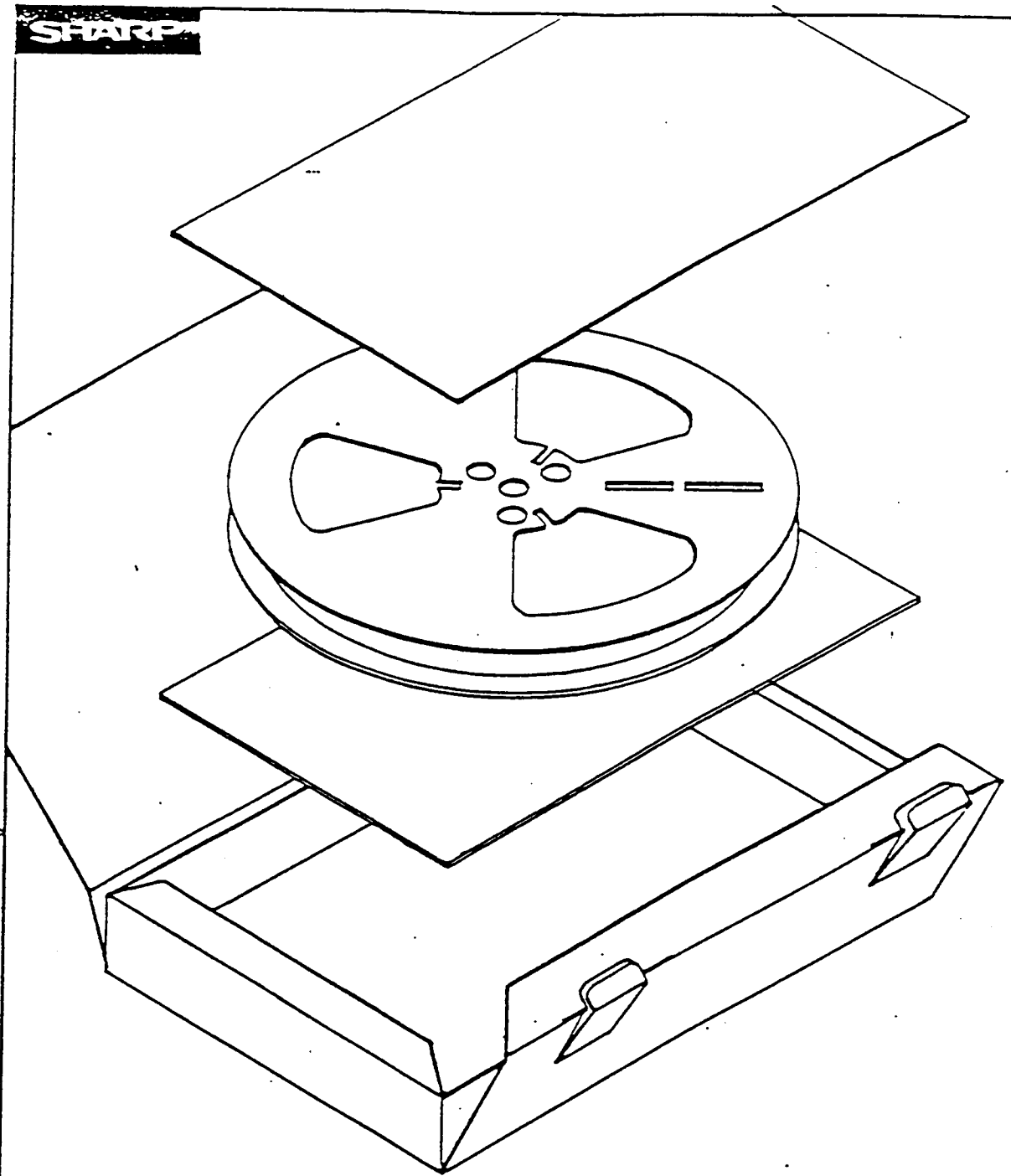


PKG	W (mm)	TAPE NUMBER
SOP14-P-225	16.4	ECR16
SOP16-P-225	"	"
SOP24-P-450	24.4	ECR24
SOP28-P-450	"	"

尺度 SCALE	単位 UNIT	△ . . .	
/	1 = m/m	△ . . .	
材質 MATERIAL	仕上 FINISH	改訂日 DATE	改訂記事 REVISION
CONDUCTIVE P S		名 称 NAME	REEL FOR EMOSS CARRIER TAPING
シャープ株式会社 IC事業部		ニ 下 CODE	
SHARP CORPORATION		図 号 DRAWING No.	C V 5 2 1



SHARP



CASE, SIZE : 350 × 342 × 56 (mm)

尺度 SCALE	単位 UNIT	△			
/	1 = /	△			
材質 MATERIAL	仕上 FINISH	改訂 DATE	改訂 記号 REVISION	REVISION	担当者 CHARGE
		名 称 NAME	EXTERNAL APPEARANCE OF PACKING CASE FOR EMBOSS CARRIER TAPING		
SHARP CORPORATION		品 番 CODE			
SHARP CORPORATION		図 号 DRAWING No	B.1	246	

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